

MA3X198 (MA198)

Silicon epitaxial planar type

For general purpose

■ Features

- Two elements contained in one package, allowing high-density mounting
- Soft recovery characteristic ($t_{rr} = 100$ ns)
- Can be connected in series

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	40	V
Repetitive peak reverse voltage	V_{RRM}	40	V
Average forward current	Single	$I_{F(AV)}$	mA
	Series	75	
Repetitive peak forward current	Single	I_{FRM}	mA
	Series	170	
Non-repetitive peak forward surge current*	Single	I_{FSM}	mA
	Series	325	
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

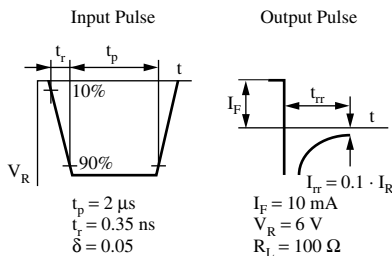
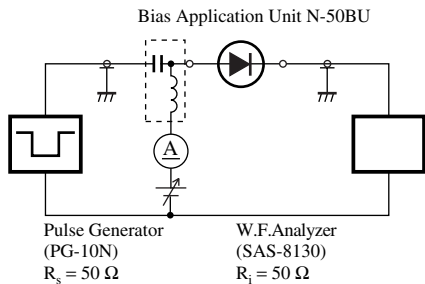
Note) *: $t = 1$ s

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

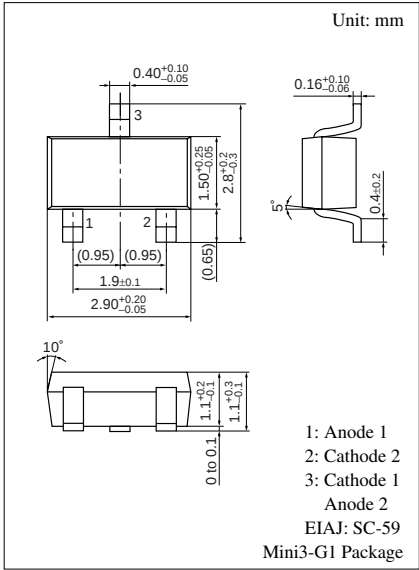
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	I_R	$V_R = 40$ V			10	nA
Forward voltage (DC)	V_{F1}	$I_F = 100$ μA	0.65		0.72	V
	V_{F2}	$I_R = 100$ mA			1.2	V
Terminal capacitance	C_t	$V_R = 6$ V, $f = 1$ MHz		1	2	pF
Reverse recovery time*	t_{rr}	$I_F = 10$ mA, $V_R = 6$ V $I_{rr} = 0.1 \cdot I_R$, $R_L = 100$ Ω			100	ns

Note) 1. Rated input/output frequency: 100 MHz

2. *: t_{rr} measuring circuit



Note) The part number in the parenthesis shows conventional part number.



Marking Symbol: M2F

Internal Connection

